



KI SEMICONDUCTOR CO.

SOT-23 Plastic-Encapsulate Diodes

BAS21_A_C_S LT1

SWITCHING DIODE

FEATURES

Power dissipation

P_D : 225 mW ($T_{amb}=25^\circ\text{C}$)

Forward Current

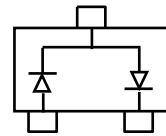
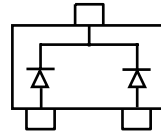
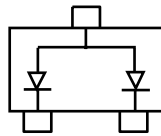
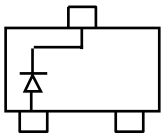
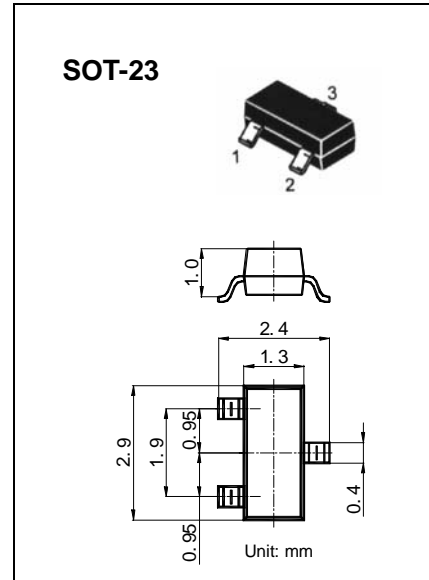
I_F : 200 mA

Reverse Voltage

V_R : 250 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$



BAS21LT1
Marking: JS

BAS21ALT1
Marking: JS2

BAS21CLT1
Marking: JS3

BAS21SLT1
Marking: JS4

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	250		V
Reverse voltage leakage current	I_R	$V_R=200\text{V}$		1	μA
Forward voltage	V_F	$I_F=100\text{mA}$ $I_F=200\text{mA}$		1000 1250	mV
Diode capacitance	C_D	$V_R=0\text{V}, f=1\text{MHz}$		5	pF
Reverse recovery time	t_{rr}			50	nS